ADE-208-399(Z)

1SV121
Silicon Epitaxial Planar PIN Diode for High Frequency Attenuator

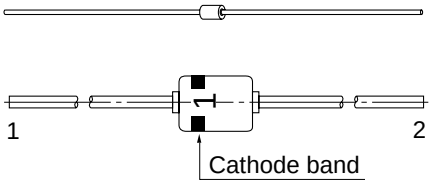
HITACHI

Rev. 0
Oct. 1995

Features

- Low capacitance.(C=0.7pF max)
- Small glass package (MHD) enables easy mounting and high reliability.

Outline



1. Cathode
2. Anode

Ordering Information

Type No.	Cathode band	Mark	Package Code
1SV121	Verdure	1	MHD

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	100	V
Forward current	I_F	100	mA
Power dissipation	P_d	250	mW
Junction temperature	T_j	175	°C
Storage temperature	T_{stg}	-65 to +175	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.1	V	I_F= 50 mA
Reverse current	I_R	—	—	100	nA	V_R= 30 V
Capacitance	C	—	—	0.7	pF	V_R = 50 V, f = 1 MHz
Forward resistance	r_{f1}	1.0	—	—	KΩ	I_F = 10 µA, f = 100 MHz
	r_{f2}	—	—	10	Ω	I_F = 10 mA, f = 100 MHz

1SV121

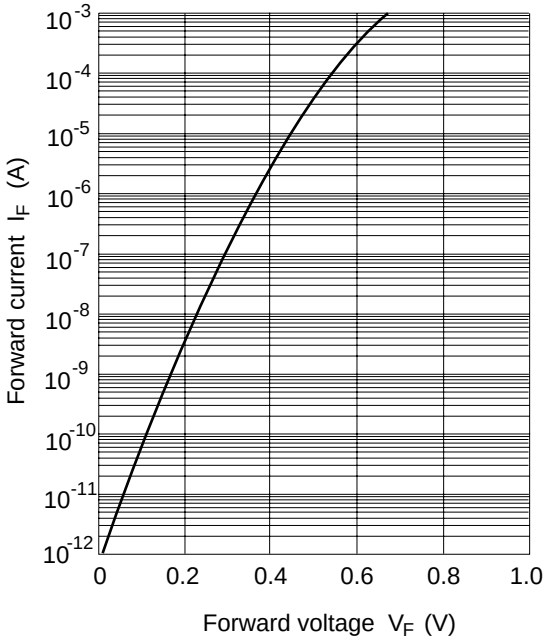


Fig.1 Forward current Vs. Forward voltage

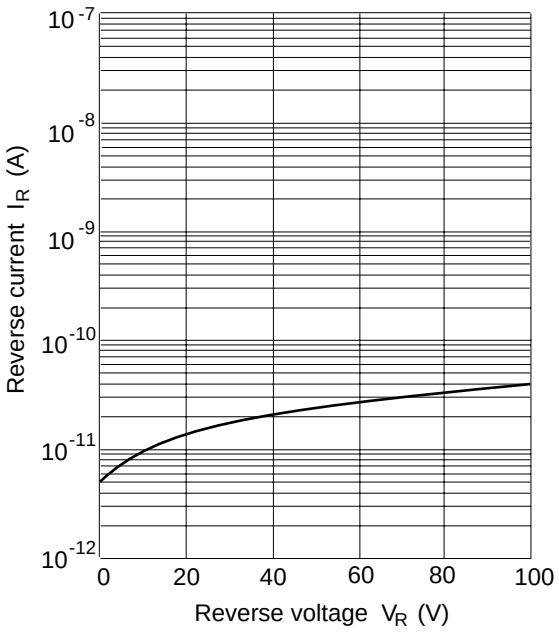


Fig.2 Reverse current Vs. Reverse voltage

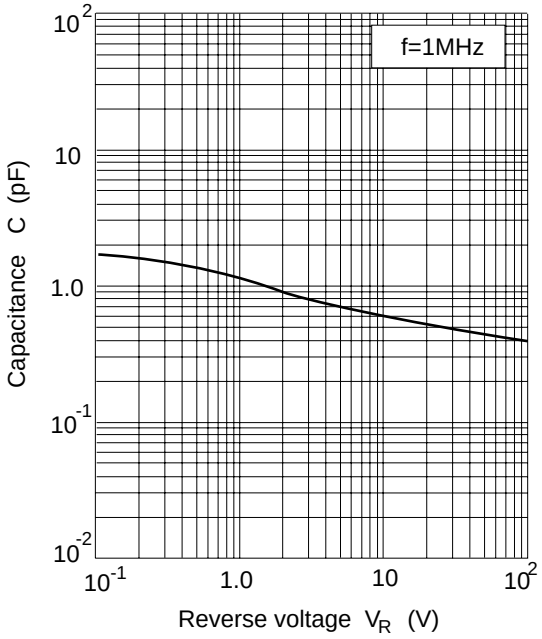


Fig.3 Capacitance Vs. Reverse voltage

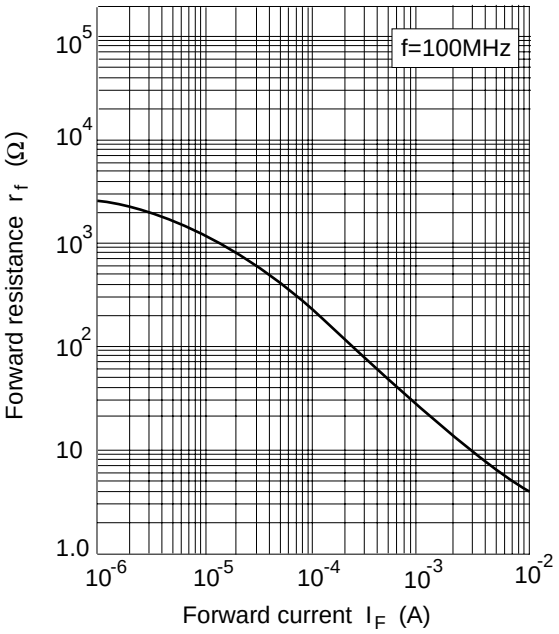
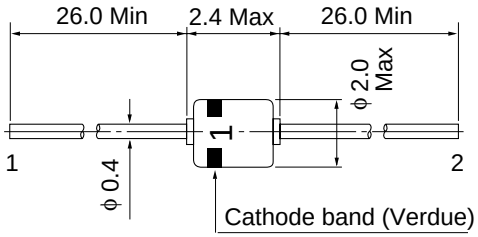


Fig.4 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm



1 Cathode
2 Anode

HITACHI Code	MHD
JEDEC Code	DO-34
EIAJ Code	—
Weight (g)	0.084